

# **TF2103U**

#### Half-Bridge Gate Driver

#### **Features**

- Floating high-side driver in bootstrap operation to 600V
- Drives two N-channel MOSFETs or IGBTs in a half bridge configuration
- Designed for enhanced performance in noisy motor applications
- 290mA source/600mA sink output current capability
- Outputs tolerant to negative transients
- Internal dead time of 420ns to protect MOSFETs
- Wide low side gate driver supply voltage: 10V to 20V
- Logic input (HIN and LIN\*) 3.3V capability
- Schmitt triggered logic inputs
- Undervoltage lockout for V<sub>cc</sub> (logic and low side supply)
- Extended temperature range: -40°C to +125°C

#### **Description**

The TF2103U is a high voltage, high speed gate driver capable of driving N-channel MOSFETs and IGBTs in a half bridge configuration. TF Semiconductors's high voltage process enables the TF2103U high side to switch to 600V in a bootstrap operation.

The TF2103U logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with controlling devices. The driver outputs feature high pulse current buffers designed for minimum driver cross conduction. TF2103U has a fixed internal deadtime of 420ns (typical).

The TF2103U is offered in a SOIC-8(N) package and operates over an extended -40 °C to +125 °C temperature range.

# **Applications**

- Motor Controls
- DC-DC Converters

**Typical Application** 

- AC-DC Inverters
- Motor Drives



SOIC-8(N)

Year Year Week Week

Up to 600V TO LOAD
÷

# **Ordering Information**

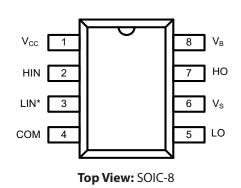
PART NUMBER	PACKAGE	PACK / Qty	MARK		
TF2103U-3AS	PDIP-8	Tube / 50	YYWW TF>TF2103U Lot ID		
TF2103U-TAU	SOIC-8(N)	Tube / 100	YYWW TF2103U		
TF2103U-TAH	SOIC-8(N)	T&R / 2500	Lot ID		

www.tfsemi.com



# **TF2103U**

#### Half-Bridge Gate Driver

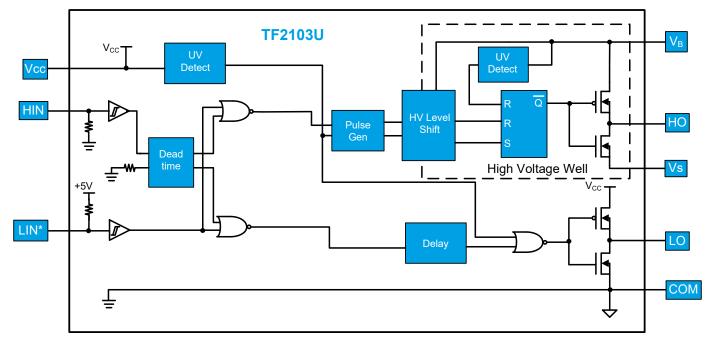


TF2103U

# **Pin Descriptions**

PIN NAME	PIN NUMBER	PIN DESCRIPTION
V <sub>cc</sub>	1	Logic and low side supply
HIN	2	Logic input for high-side gate driver output in phase with HO
LIN*	3	Logic input for low-side gate driver output out of phase with LO
СОМ	4	Low-side and logic return
LO	5	Low-side gate drive output
V <sub>s</sub>	6	High-side floating supply return
НО	7	High-side gate drive output
V <sub>B</sub>	8	High-side floating supply

# **Functional Block Diagram**





# TF2103U Half-Bridge Gate Driver

### Absolute Maximum Ratings (NOTE1)

V <sub>B</sub> - High side floating supply voltage0.3V to +624V
$V_s$ - High side floating supply offset voltageV <sub>B</sub> -24V to V <sub>B</sub> +0.3V
$V_{HO}$ -Highside floating output voltageV <sub>s</sub> -0.3V to V <sub>B</sub> +0.3V
$dV_s/dt$ - Offset supply voltage transient50 V/ns

V <sub>cc</sub> - Low-side fixed supply voltage	0.3V to +24V
V <sub>10</sub> - Low-side output voltage	0.3VtoV <sub>cc</sub> +0.3V
V <sub>IN</sub> - Logic input voltage (HIN and LIN*)	cc

**NOTE1** Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

$P_{D}$ - Package power dissipation at $T_{A} \le 25 \text{ °C}$ SOIC-80.625W	
SOIC-8(N) Thermal Resistance <i>(NOTE2)</i> θ <sub>JA</sub> 200 °C/W	
T <sub>J</sub> - Junction operating temperature+150 °C T <sub>L</sub> - Lead Temperature (soldering, 10 seconds)+300 °C T <sub>stq</sub> - Storage temerature55 to 150 °C	

**NOTE2** When mounted on a standard JEDEC 2-layer FR-4 board.

#### **Recommended Operating Conditions**

Symbol	Parameter	MIN	MAX	Unit
V <sub>B</sub>	High side floating supply absolute voltage	V <sub>s</sub> + 10	V <sub>s</sub> + 20	V
V <sub>s</sub>	High side floating supply offset voltage	NOTE3	600	V
V <sub>HO</sub>	High side floating output voltage	Vs	V <sub>B</sub>	V
V <sub>cc</sub>	Low side fixed supply voltage	10	20	V
V <sub>LO</sub>	Low side output voltage	0	V <sub>cc</sub>	V
V <sub>IN</sub>	Logic input voltage (HIN and LIN*)	0	5	V
T <sub>A</sub>	Ambient temperature	-40	125	°C

**NOTE3** Logic operational for VS of -5V to +600V.



# TF2103U

#### Half-Bridge Gate Driver

# DC Electrical Characteristics (NOTE4)

 $V_{\text{BIAS}}(V_{\text{CC}},V_{\text{BS}})$  = 15V,  $T_{\text{A}}$  = 25 °C , unless otherwise specified.

Symbol	Parameter	Conditions	MIN	ТҮР	МАХ	Unit
V <sub>IH</sub>	Logic "1" (HIN) & Logic "0" (LIN*) input voltage	$V_{cc} = 10V$ to 20V	2.5			
V <sub>IL</sub>	Logic "0" (HIN) & Logic "1" (LIN*) input voltage	- NOTES			0.8	v
V <sub>OH</sub>	High level output voltage, $V_{BIAS}$ - $V_{O}$	$I_0 = 2mA$		0.05	0.2	
V <sub>ol</sub>	Low level output voltage, V <sub>o</sub>	$I_0 = 2mA$		0.02	0.1	
I <sub>LK</sub>	Offset supply leakage current	VB = VS = 600V			50	
I <sub>BSQ</sub>	Quiescent V <sub>BS</sub> supply current	$V_{IN} = 0V \text{ or } 5V$		7	50	
I <sub>ccq</sub>	Quiescent V <sub>cc</sub> supply current	$V_{IN} = 0V \text{ or } 5V$		350	500	μA
I <sub>IN+</sub>	Logic "1" input bias current	$HIN = 5V, LIN^* = 0V$		3	10	
I <sub>IN-</sub>	Logic "0" input bias current	$HIN = 0V, LIN^* = 5V$			5	
V <sub>CCUV+</sub>	V <sub>cc</sub> supply under-voltage positive going threshold		7.0	8.4	9.8	
V <sub>ccuv-</sub>	V <sub>cc</sub> supply under-voltage negative going threshold		6.5	7.8	9.3	V
V <sub>BSUV+</sub>	V <sub>BS</sub> supply under-voltage positive going threshold		3.6	4.5	5.6	V
V <sub>BSUV-</sub>	V <sub>BS</sub> supply under-voltage negative going threshold		3	3.7	4.6	V
I <sub>0+</sub>	Output high short circuit pulsed current	$V_{o} = 0V$ , PW $\leq 10 \ \mu s$	130	300		
I <sub>0-</sub>	Output low short circuit pulsed current	$V_0 = 15V$ , PW $\leq 10 \ \mu s$	270	550		mA

**NOTE4** The  $V_{INV}V_{TIV}$  and  $I_{IN}$  parameters are applicable to the two logic input pins: HIN and LIN\*. The  $V_o$  and  $I_o$  parameters are applicable to the respective output pins: HO and LO. **NOTE5** For optimal operation, it is recommended that the input pulse (to IN and SD\*) should have an amplitude of 2.5V minimum with a pulse width of 840ns minimum.

**TF2103U** 



Half-Bridge Gate Driver

# **AC Electrical Characteristics** $V_{BIAS}(V_{CC'}, V_{BS}) = 15V, C_{L} = 1000 \text{pF}, \text{ and } T_{A} = 25 \text{ °C}$ , unless otherwise specified.

Symbol	Parameter	Conditions	MIN	ТҮР	MAX	Unit
t <sub>on</sub>	Turn-on propagation delay	$V_s = 0V$		560	820	
t <sub>off</sub>	Turn-off propagation delay	$V_{s} = 600V$		150	220	
t <sub>DM</sub>	Delay matching, HS & LS turn-on/turn-off				70	
t <sub>r</sub>	Turn-on rise time			80	170	ns
t <sub>r</sub>	Turn-off fall time	$V_s = 0V$		35	90	
t <sub>DT</sub>	Deadtime: t <sub>DT LO-HO</sub> & t <sub>DT HO-LO</sub>		300	420	650	

#### TF2103U

#### Half-Bridge Gate Driver

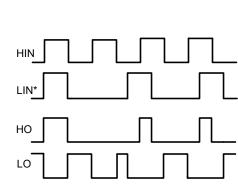


Figure 1. Input / Output Timing Diagram

TF Semiconductor Solutions

**Timing Waveforms** 

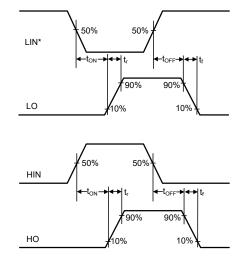


Figure 2. Switching Time Waveform Definitions

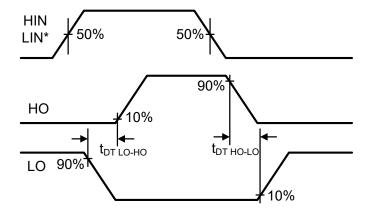


Figure 3. Deadtime Waveform Definitions





Half-Bridge Gate Driver

### **Application Information**

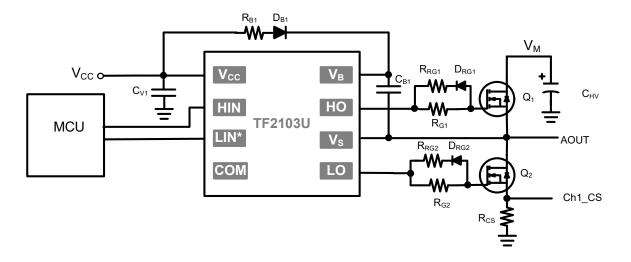


Figure 4. Single phase (of four) for Stepper motor driver application using the TF2103U

**RRG1** and RRG2 values are typically between  $0\Omega$  and  $10\Omega$ , exact value decided by MOSFET junction capacitance and drive current of gate driver;  $10\Omega$  is used in this example.

**R**G1 and RG2 values are typically between  $20\Omega$  and  $100\Omega$ , exact value decided by MOSFET junction capacitance and drive current of gate driver;  $50\Omega$  is used in this example.

**R**B1 value is typically between  $3\Omega$  and  $20\Omega$ , exact value depending on bootstrap capacitor value and amount of current limiting required for bootstrap capacitor charging;  $10\Omega$  is used in this example. Also DB should be an ultra fast diode of 1A rating minimum and voltage rating greater than system operating voltage.

■ It is recommended that the input pulse (to HIN and LIN\*) should have an amplitude of 2.5V minimum (for VDD=15V) with a minimum pulse width of 840ns.

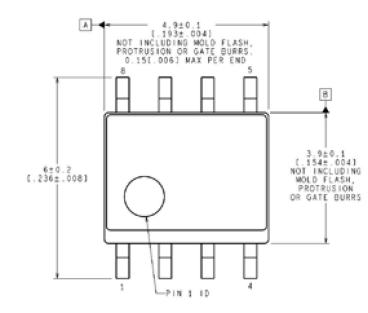
**TF2103U** 

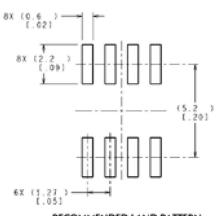


Half-Bridge Gate Driver

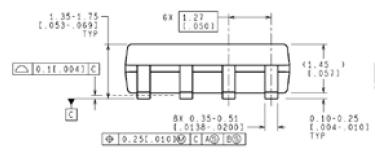
# Package Dimensions (SOIC-8 N)

Please contact support@telefunkensemi.com for package availability.



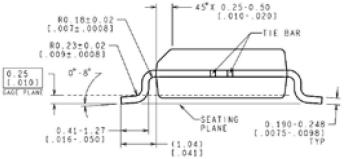


RECOMMENDED LAND PATTERN



NOTES: UNLESS OTHERWISE SPECIFIED

1. REFERENCE JEDEC REGISTRATION MS-012, VARIATION AA.



CONTROLLING DIMENSION IS MILLIMETER VALUES IN [ ] ARE INCHES DIMENSIONS IN [ ] FOR REFERENCE ONLY

TF2103U



#### Half-Bridge Gate Driver

Rev.	Change	Owner	Date
1.0	First release, AI datasheet	Keith Spaulding	10/10/2018
1.1	Edit electrical specs with first silicon evaluation	Keith Spaulding	8/12/2019
1.2	Add Application Information	Duke Walton	8/26/2020

#### **Important Notice**

TF Semiconductor Solutions (TFSS) PRODUCTS ARE NEITHER DESIGNED NOR INTENDED FOR USE IN MILITARY AND/OR AEROSPACE, AUTOMOTIVE OR MEDICAL DEVICES OR SYSTEMS UNLESS THE SPECIFIC TFSS PRODUCTS ARE SPECIFICALLY DESIGNATED BY TFSS FOR SUCH USE. BUYERS ACKNOWLEDGE AND AGREE THAT ANY SUCH USE OF TFSS PRODUCTS WHICH TFSS HAS NOT DESIGNATED FOR USE IN MILITARY AND/OR AEROSPACE, AUTOMOTIVE OR MEDICAL DEVICES OR SYSTEMS IS SOLELY AT THE BUYER'S RISK.

TFSS assumes no liability for application assistance or customer product design. Customers are responsible for their products and applications using TFSS products.

Resale of TFSS products or services with statements different from or beyond the parameters stated by TFSS for that product or service voids all express and any implied warranties for the associated TFSS product or service. TFSS is not responsible or liable for any such statements.

©2020 TFSS. All Rights Reserved. Information and data in this document are owned by TFSS wholly and may not be edited , reproduced, or redistributed in any way without the express written consent from TFSS.

For additional information please contact support@tfsemi.com or visit www.tfsemi.com